

N-Channel Enhancement Mode MOSFET

1. Product Information

1.1 Features

- ☒ Surface-mounted package
- ☒ T_J max 175°C
- ☒ Advanced trench cell design
- ☒ MSL1

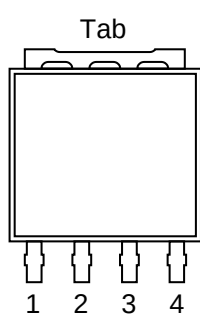
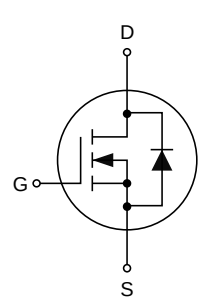
1.2 Applications

- ☒ Power appliances
- ☒ E-Tool appliances
- ☒ High power inverter system
- ☒ Load switching

1.3 Quick reference

- ☒ $BV \geq 60\text{ V}$
- ☒ $P_D \leq 187.5\text{ W}$
- ☒ $I_D \leq 295\text{ A}$
- ☒ $R_{DS(ON)} \leq 1.0\text{ m}\Omega @ V_{GS}=10\text{ V}$

2. Pin Description

Pin	Description	Simplified Outline	Symbol
1,2,3	Source	 Top View LFPAK 5x6	
4	Gate		
Tab	Drain		

3. Limiting Values

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	Drain-Source Voltage	$T_C=25^{\circ}\text{C}$	60	-	V
V_{GS}	Gate-Source Voltage	$T_C=25^{\circ}\text{C}$	-	± 20	V
$I_D^{*,***}$	Drain Current (DC)	$T_C=25^{\circ}\text{C}, V_{GS}=10\text{ V}$	-	295	A
		$T_C=100^{\circ}\text{C}, V_{GS}=10\text{ V}$	-	209	A
I_{DM}^{*}	Drain Current (Pulsed)	$T_C=25^{\circ}\text{C}, V_{GS}=10\text{ V}$	-	1180	A
P_D	Drain Power Dissipation	$T_C=25^{\circ}\text{C}$	-	187.5	W
T_J, T_{stg}	Operating Junction and Storage Temperature Range		-55	175	$^{\circ}\text{C}$
I_S	Continuous-Source Current	$T_C=25^{\circ}\text{C}$	-	295	A
E_{AS}	Single Pulsed Avalanche Energy	$V_{DD}=40\text{ V}, L=0.3\text{ mH}$	-	735	mJ
$R_{\theta JA}^{**}$	Thermal Resistance, Junction to Ambient		-	39	$^{\circ}\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case		-	0.8	$^{\circ}\text{C/W}$

Notes:

- * Pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- ** Surface mounted on 1 in² pad area, $t \leq 10\text{ sec}$.
- *** Limited by bonding wire.

4. Marking Information

Product Name	Marking
KJ009N06LF	KJ009N06LF XXXXXX-X

5. Ordering Code

Product Name	Package	Reel size	Tape width	Quantity (pcs)
KJ009N06LF	LFPK 5x6	13"	12 mm	5000

Note: KUAJIEXIN defines "Green" as lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900 ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500 ppm by weight; Follow IEC 61249-2-21 and IPC/JEDEC J-STD-020C).

6. Electrical Characteristics (T_A=25°C unless otherwise noted)

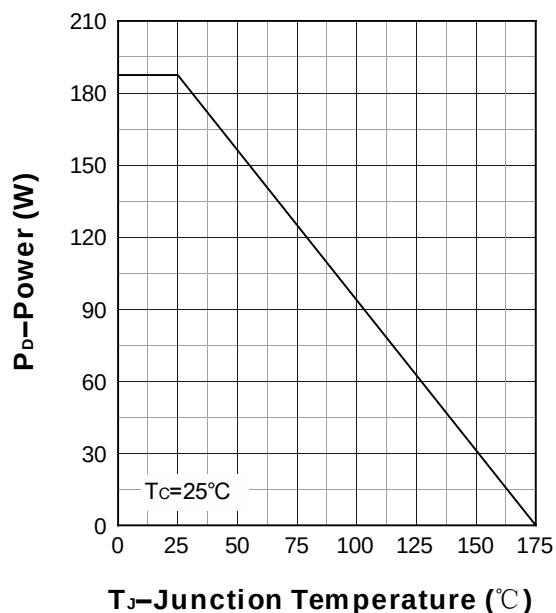
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0 V, I _{DS} =250 μA	60	-	-	V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250 μA	1.2	1.7	2.5	V
I _{DSS}	Drain Leakage Current	V _{DS} =60 V, V _{GS} =0 V	-	-	1	μA
I _{GSS}	Gate Leakage Current	V _{GS} =0 V, V _{GS} =±20 V	-	-	±100	nA
R _{DS(ON)} ^a	On-State Resistance	V _{GS} =10 V, I _{DS} =20 A	-	0.85	1.0	mΩ
Diode Characteristics						
V _{SD} ^a	Diode Forward Voltage	I _{SD} =20 A, V _{GS} =0 V	-	0.7	1.2	V
t _{rr}	Reverse Recovery Time	I _{SD} =20 A, V _{GS} =0 V dI _{SD} /dt=100 A/μs	-	80	-	ns
Q _{rr}	Reverse Recovery Charge		-	119	-	nC
Dynamic Characteristics ^b						
C _{iss}	Input Capacitance	V _{GS} =0 V, V _{DS} =30 V, Frequency=1 MHz	-	6530	-	pF
C _{oss}	Output Capacitance		-	2945	-	
C _{rss}	Reverse Transfer Capacitance		-	120	-	
t _{d(on)}	Turn-on Delay Time	V _{DS} =30 V, V _{GEN} =10 V, R _G =3 Ω, R _L =0.6 Ω, I _{DS} =20 A	-	7	-	ns
t _r	Turn-on Rise Time		-	15	-	
t _{d(off)}	Turn-off Delay Time		-	110	-	
t _f	Turn-off Fall Time		-	45	-	
Gate Charge Characteristics ^b						
Q _g	Total Gate Charge	V _{DS} =30 V, V _{GS} =10 V, I _{DS} =20 A	-	125	-	nC
Q _{gs}	Gate-Source Charge		-	18	-	
Q _{gd}	Gate-Drain Charge		-	23	-	

Notes:

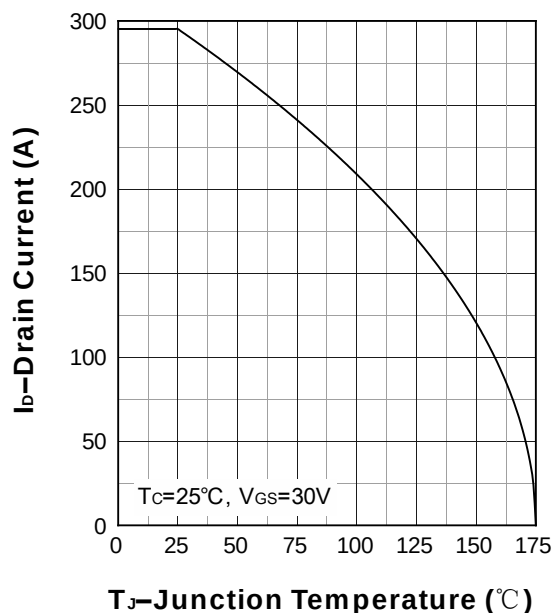
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
b. Guaranteed by design, not subject to production testing.

7. Typical Characteristics

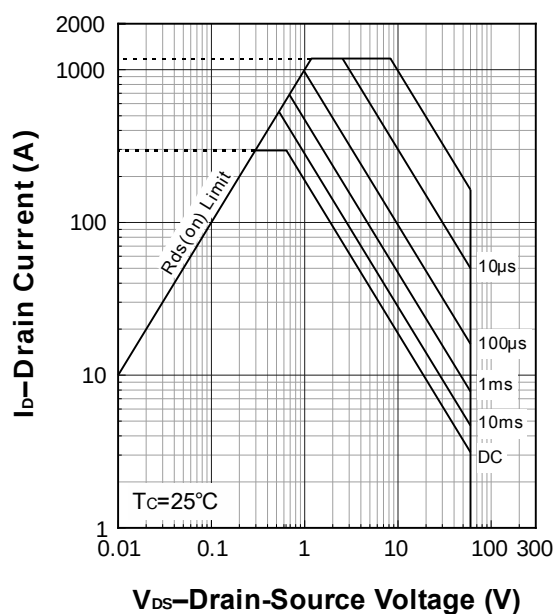
Power Capability



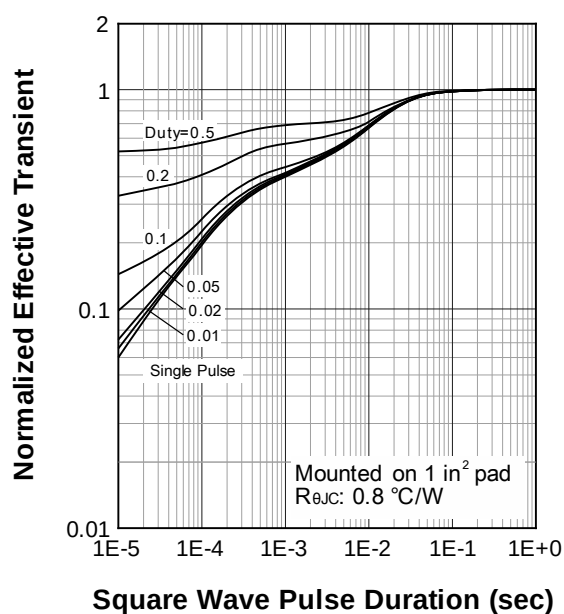
Current Capability



Safe Operating Area

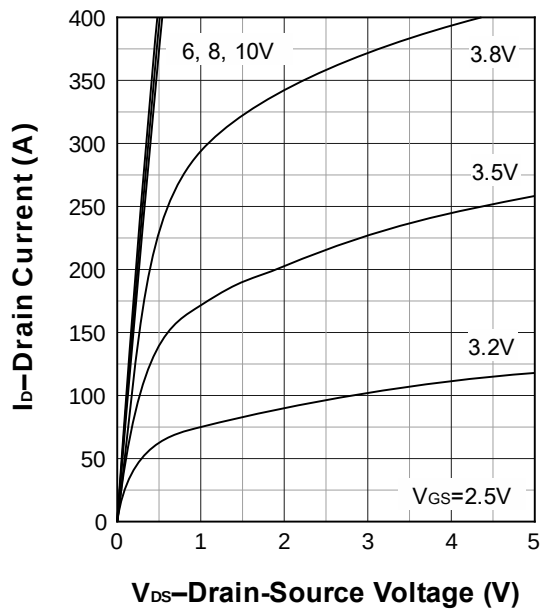


Transient Thermal Impedance

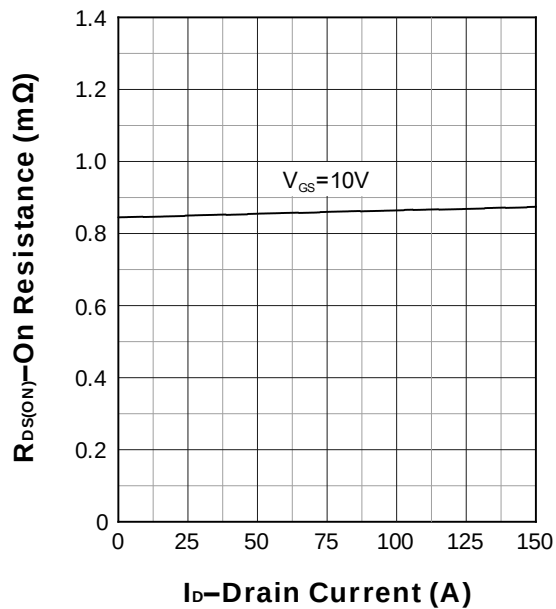


7. Typical Characteristics (cont.)

Output Characteristics

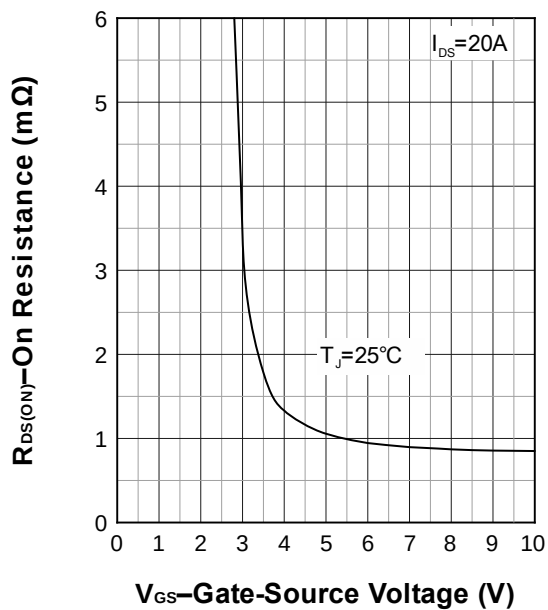


On Resistance

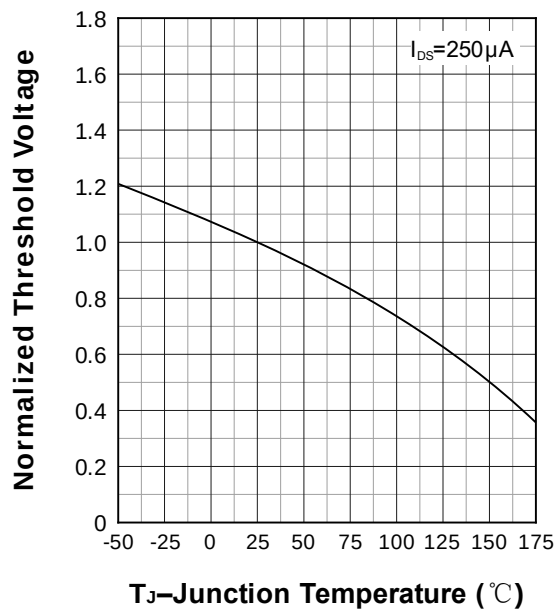


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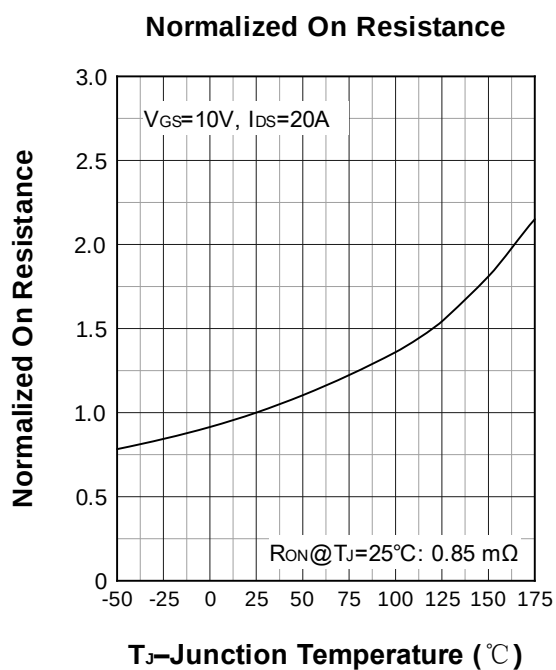
Transfer Characteristics



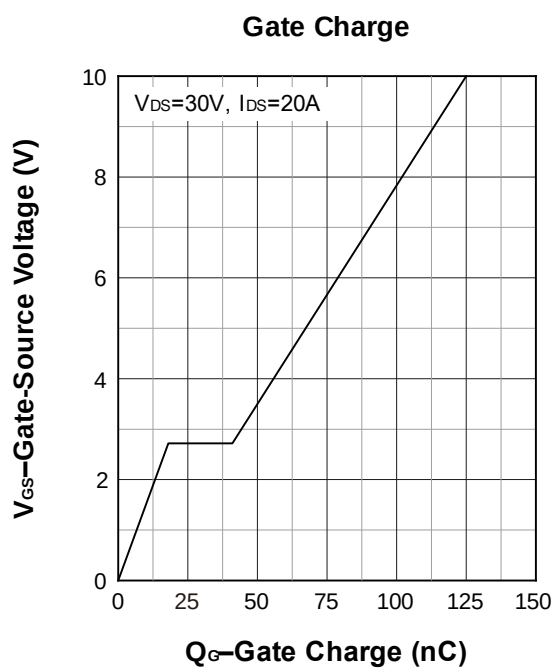
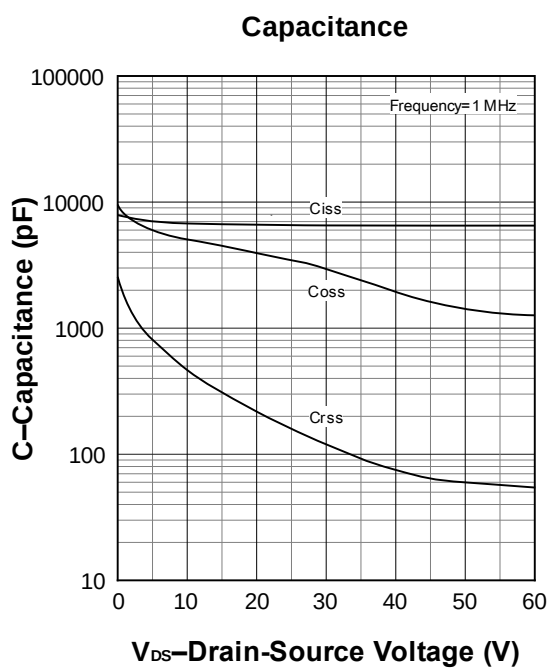
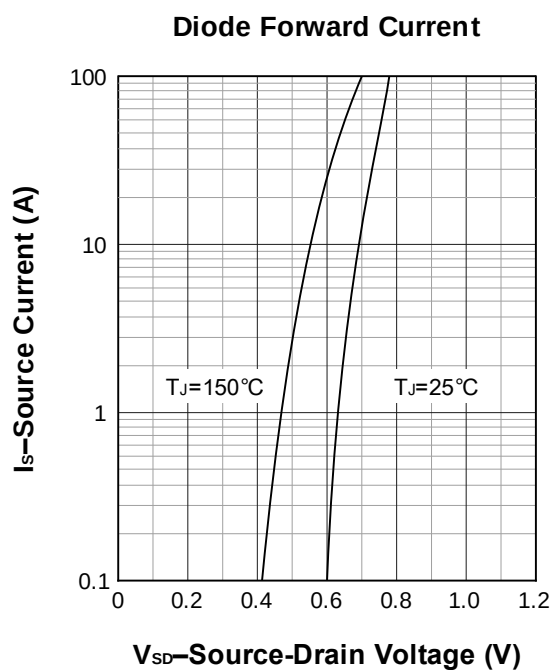
Normalized Threshold Voltage



7. Typical Characteristics (cont.)

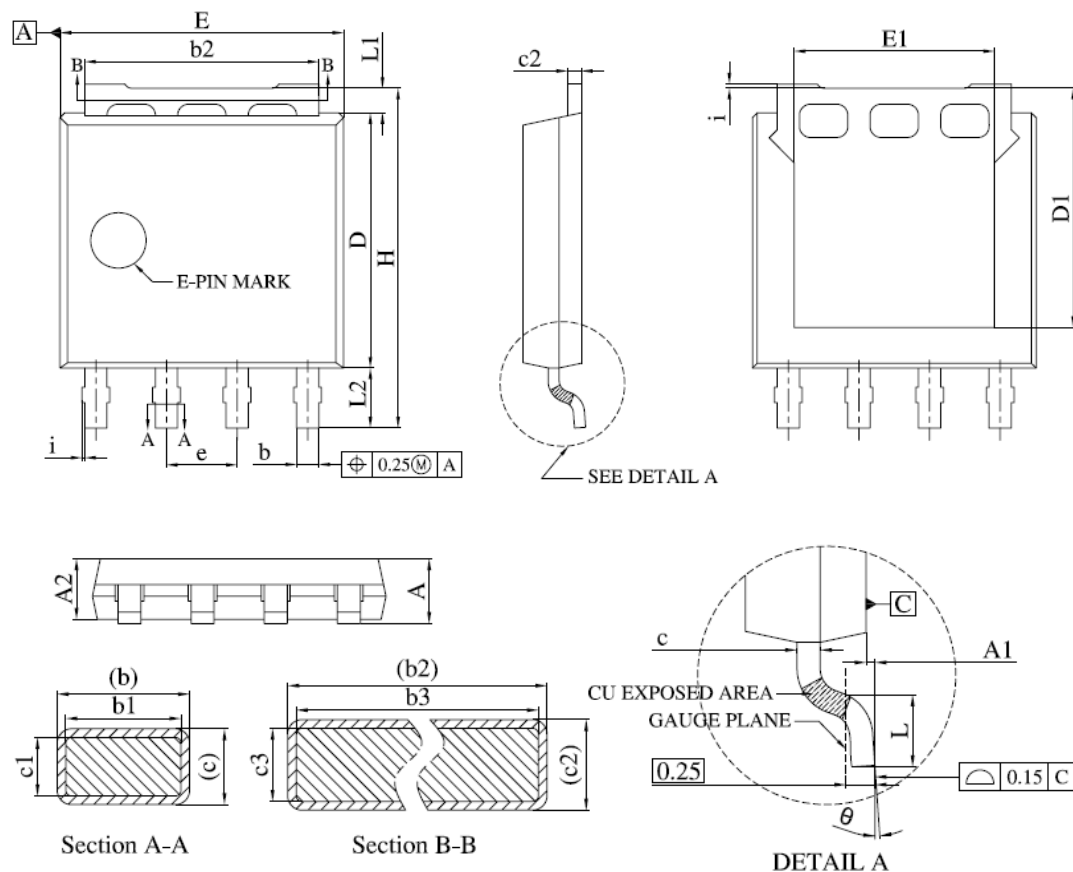


40



8. Package Dimensions

LFPAK5x6 Package



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	1.00	1.30
A1	0	0.15
A2	0.98	1.12
b	0.35	0.50
b1	0.32	0.46
b2	4.02	4.41
b3	4.00	4.37
c	0.19	0.25
c1	0.17	0.23
c2	0.24	0.30
c3	0.22	0.28

Symbol	Dimensions in Millimeters	
	MIN.	MAX.
D	4.45	4.70
D1	-	4.45
E	4.95	5.30
E1	3.50	3.70
e	1.27 BSC	
H	5.95	6.25
i	-	0.25
L	0.40	0.85
L1	0.27	0.57
L2	0.80	1.30
θ	0°	8°